L Number	Hits	Search Text	DB	Time stamp
18	4	(laser near diode) and (third near clad\$4) and active	USPAT;	2003/08/25 09:36
		and contact and electrode and (injection near3 stripe)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
19	6	(laser) and (third near clad\$4) and active and contact	USPAT;	2003/08/25 10:08
19	0		US-PGPUB;	2003/00/23 10:00
		and electrode and (injection near3 stripe)		
			EPO; JPO;	
1		,	DERWENT;	
			IBM_TDB	
20	2	(laser) and (third near clad\$4) and active and contact	USPAT;	2003/08/25 10:02
		and electrode and (injection near3 stripe) and	US-PGPUB;	}
		((electrode or contact) near (second near clad\$4))	EPO; JPO;	
		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	DERWENT;	
			IBM TDB	
21	0	(laser) and (third near clad\$4) and active and contact	USPAT;	2003/08/25 10:04
21	U			2003/08/25 10:04
		and electrode and (injection near3 stripe) and	US-PGPUB;	
		((electrode) near (second near clad\$4))	EPO; JPO;	
			DERWENT;	
		'	IBM_TDB	
22	34	(laser) and ((electrode) near (second near clad\$4))	USPAT;	2003/08/25 10:05
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	00	// / / / / / / / / / / / / / / / / / /		2002/00/25 10:05
23	23	(laser) and ((electrode) near (second near clad\$4))	USPAT	2003/08/25 10:05
24	6	(laser) and (third near clad\$4) and active and	USPAT;	2003/08/25 10:15
·		(contact near (layer or region or medium)) and	US-PGPUB;	
ľ		electrode and (injection near3 stripe)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
26	Ż	(laser) and (third near clad\$4) and active and	USPAT	2003/08/25 10:15
20	~	(contact near (layer or region or medium)) and	00.7.	2000/00/20 10:10
		· ·		ŀ
	00	(electrode with clad\$4) and (injection near3 stripe)		0000/00/05 00 04
-	33	(laser near diode) and clad\$4 and active and contact	USPAT;	2003/08/25 09:31
		and electrode and (injection near3 stripe) and voltage	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	·		IBM TDB	
_	26	((laser near diode) and clad\$4 and active and contact	USPAT;	2003/04/02 14:55
	2.5	and electrode and (injection near3 stripe) and	US-PGPUB;	
		voltage) and 372/\$	EPO; JPO;	
		Voltage/ and 372/9	DERWENT;	
			1	
			IBM_TDB	
-	53	laser and clad\$4 and active and contact and	USPAT;	2003/04/03 09:01
		electrode and (injection near3 stripe) and voltage	US-PGPUB;	
			EPO;-JPO;	
			DERWENT;	
			IBM TDB	
_	10	laser and clad\$4 and active and contact and	USPAT;	2003/04/03 06:12
		electrode and (injection near stripe) and voltage	US-PGPUB;	
		occurace and impostion hear surper and voltage	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	29	laser and clad\$4 and active and contact and	USPAT;	2003/04/03 08:47
	İ	electrode and (injection near2 stripe) and voltage	US-PGPUB;	j
			EPO; JPO;	
			1	1
	l		DERWENT;	

-	2	laser and clad\$4 and active and contact and	USPAT;	2003/04/03 16:07
		electrode and (injection near2 stripe) and voltage and	US-PGPUB;	
		(etching near stop near (layer or region or medium or	EPO; JPO;	
		film))	DERWENT;	
		, ·	IBM_TDB	
-	2	laser and clad\$4 and active and contact and	USPAT;	2003/04/03 16:06
		electrode and (injection near2 stripe) and voltage and	US-PGPUB;	
		(etch\$4 near stop)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	12.	laser and clad\$4 and active and contact and	USPAT;	2003/04/03 08:57
		electrode and (injection near2 stripe) and voltage and	US-PGPUB;	
		(etch\$4 near (layer or region or medium or film))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	. 1	(laser and clad\$4 and active and contact and	USPAT;	2003/04/03 08:57
		electrode and (injection near2 stripe) and voltage and	US-PGPUB;	
		(etch\$4 near (layer or region or medium or film)))	EPO; JPO;	
		and third near clad	DERWENT;	
			IBM_TDB	
-	1	(laser and clad\$4 and active and contact and	USPAT;	2003/04/03 09:09
		electrode and (injection near2 stripe) and voltage and	US-PGPUB;	
		(etch\$4 near (layer or region or medium or film)))	EPO; JPO;	
		and third near clad\$4	DERWENT;	
			IBM_TDB	
	364	((laser or diode) with (ridge or stripe)) and clad\$4	USPAT;	2003/04/03 09:06
•		and active and contact and electrode and voltage	US-PGPUB;	
		and 372/46	EPO; JPO;	
		•	DERWENT;	
1			IBM_TDB	
-	. 137	((laser NEAR diode) with (ridge or stripe)) and	USPAT;	2003/04/03 09:07
		clad\$4 and active and contact and electrode and	US-PGPUB;	
		voltage	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	12	(((laser NEAR diode) with (ridge or stripe)) and	USPAT;	2003/04/03 09:21
		clad\$4 and active and contact and electrode and	US-PGPUB;	
		voltage) and third near clad\$4	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5	((((laser NEAR diode) with (ridge or stripe)) and	USPAT;	2003/04/03 13:02
		clad\$4 and active and contact and electrode and	US-PGPUB;	
		voltage) and third near clad\$4) and 372/46	EPO; JPO;	
		•	DERWENT;	
		AUTO NIEAR III AND	IBM_TDB	0000/04/00 44 01
-	60	(((laser NEAR diode) with (ridge or stripe)) and	USPAT;	2003/04/03 14:04
		clad\$4 and active and contact and electrode and	US-PGPUB;	
		voltage) and 372/46	EPO; JPO;	·
			DERWENT;	
		Manage NEAD Madely 100 Address and 150 A	IBM_TDB	2002/04/02 44:00
-	111	((laser NEAR diode) with (ridge or stripe)) and	USPAT;	2003/04/03 14:06
		(clad\$4 near (layer or region or medium or film)) and	US-PGPUB;	
		(active near (layer or region or medium or film)) and	EPO; JPO; DERWENT;	
		(contact near (layer or region or medium or film)) and electrode and 372/46	IBM TDB	
	52	(((laser NEAR diode) with (ridge or stripe)) and	USPAT;	2003/04/03 14:10
-	52	((laser NEAR diode) with (ridge or stripe)) and (clad\$4 near (layer or region or medium or film)) and	US-PGPUB;	2003/04/03 14:10
		(active near (layer or region or medium or film)) and	EPO; JPO;	
		(contact near (layer or region or medium or film)) and	DERWENT;	
		electrode and 372/46) and voltage	IBM TDB	
L		electrone and 372/40/ and voltage	מטו ואוטו	

(calds4 near (layer or region or medium or film)) and (active near (layer or region or medium or film)) and electrode and 372/46 and third near clads4 clads and laser near diode and (etch4 near stop) clads and (laser near diode) and (etch54 near stop) clads and (laser near diode) and (etch54 near stop) clads and (laser near diode) and (etch54 near stop) clads and (laser near diode) and (etch54 near stop) clads and (laser near diode) and (etch54 near stop) clads and (laser near diode) and (etch54 near stop) clads and (laser near diode) and (etch54 near stop) clads and (laser near diode) and (etch54 near stop) blaser and clads4 and active and contact and electrode and (injection near/2 stripe) and (etching near stop near (layer or region or medium or film)) alser and clads4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) delectrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturation enear diverde and ridge or stripe) and (etching near stop near (layer or region or medium or film)) and 372/46) and saturable near absorption delectrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and 372/46) and saturable near absorption delectrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and 372/46) and saturable near absorption delectrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and 372/46) and saturable near absorption delectrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and 372/46) and saturable near absorption delectrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and 372/46 and saturable near absorption delectrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and 372/46 and saturable near absorption delectrode and (ridge or st					
(contact near (layer or region or medium or film)) and clectrode and 372/46) and third near clad \$4 clad \$ and laesr near diode and (etch\$4 near stop) 2003/04/03 16:06 3200 clad \$ and (laser near diode) and (etch\$4 near stop) clad \$ and (laser near diode) and (etch\$4 near stop) clad \$ and (laser near diode) and (etch\$4 near stop) clad \$ and (laser near diode) and (etch\$4 near stop) clad \$ and (laser near diode) and (etch\$4 near stop) clad \$ and (laser near diode) and (etch\$4 near stop) clad \$ and (laser near diode) and (etch\$4 near stop) clad \$ and (laser near diode) and (etch\$4 near stop) clad \$ and (laser near diode) and (etch\$4 near stop) clad \$ and (laser near diode) and (etch\$4 near stop) clad \$ and (laser near diode) and (etch\$4 near stop) clad \$ and (laser near diode) and (etch\$4 near stop) clad \$ and clad \$ and active and contact and electrode and (injection near) stopic near (layer or region or medium or film)) and lectrode and (ridge or stripe) and letching near stopic near (layer or region or medium or film)) and lectrode and (ridge or stripe) and letching near stopic near (layer or region or medium or film)) and 372/46 electrode and (ridge or stripe) and letching near stopic near (layer or region or medium or film)) and 372/46 and saturable near absorption and electrode and (ridge or stripe) and letching near stopic near (layer or region or medium or film)) and 372/46 and saturable near absorption and electrode and ridge or stripe) and letching near stopic near (layer or region or medium or film)) and 372/46 and saturable near absorption and electrode and ridge or stripe) and letching near stopic near (layer or region or medium or film)) and 372/46 and saturable near absorption and 372/46 [laser near diode) and clad \$4 and active and contact and electrode and ridge or stripe) and letching near stopic near (layer or region or medium or film)) and saturable near absorption and 372/46 [laser near diode) and clad \$4 and active and contact and electrode and ridge or stripe) and letc	-	. 10		· ·	.2003/04/03 14:10
contact near (layer or region or medium or film)) and saturable near stoppeor or medium or film) and saturable near stoppeor or medium or film)) and saturable near absorption as stop near (layer or region or medium or film)) and saturable near absorption or medium or film)) and saturable near absorption and 372/46 and saturable near absorption as stop near (layer or region or medium or film)) and saturable near absorption and 372/46 and saturable near absorption as stop near (layer or region or medium or film)) and saturable near absorption and 372/46 and saturable near absorption as stop near (layer or region or medium or film)) and saturable near absorption and 372/46 and saturable near abso				l .	
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Lis-RGPUB; PO; DERWENT; IBM, TDB US-RAT; US-RGPUB; PO; JPO; JPO; PO; PO; JPO; J		•		_	2002/04/02 16:06
258 clad\$ and (laser near diode) and (etch\$4 near stop) 258 clad\$ and (laser near diode) and (etch\$4 near stop) 258 clad\$ and (laser near diode) and (etch\$4 near stop) 258 clad\$ and (laser near diode) and (etch\$4 near stop) 258 clad\$ and (laser near diode) and (etch\$4 near stop) 259 clad\$ and (laser near diode) and (etch\$4 near stop) 2503/04/03 16:08 259 clad\$ and (laser near diode) and (etch\$4 near stop) 259 clad\$ and active and contact and electrode and (inigetion near2 stripe) and (etching) 2503/04/03 16:08 259 clad\$ and active and contact and electrode and (inige or stripe) and (etching near stop) 2503/04/03 16:08 259 clad\$ and active and contact and electrode and (inige or stripe) and (etching near stop) 2503/04/03 16:08 259 clad\$ and active and contact and electrode and (inige or stripe) and (etching near stop) 2503/04/03 16:08 2503/04/03 16:39 2503/04/03 16:39 2503/04/03 16:35 2503/04/03 16:35 2503/04/03 16:35 2503/04/03 16:35 2503/04/03 16:35 2503/04/03 16:35 2503/04/03 16:35 2503/04/03 16:35 2503/04/03 16:35 2503/04/03 16:35 2503/04/03 16:35 2503/04/03 16:35 2503/04/03 16:35	-	0	clads and laesr near diode and (etch\$4 near stop)		2003/04/03 16:06
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258 clad\$ and (laser near diode) and (etch\$4 near stop near layer) 1				—	00001041004007
clad\$ and (laser near diode) and (etch\$4 near stop DERWENT; IBM_TDB USPAT; USPGPUB; DERWENT; IBM_TDB USPAT; DERWENT; IBM_TDB U	-	320	clad\$ and (laser near diode) and (etch\$4 near stop)	· ·	2003/04/03 16:07
Lad\$ and (laser near diode) and (etch\$4 near stop near layer) Liser and clad\$4 and active and contact and electrode and (injection near2 stripe) and (etching near stop near (layer or region or medium or film)) Baser and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) (laser and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) (laser and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) (laser and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and 372/46 plots (laser and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and 372/46 plots (laser and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and 372/46 plots (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and 372/46 plots (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption and 372/46 plots (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption ear stop near (layer or region or medium or film)) and saturable near absorption ear stop near (layer or region or medium or film) and saturable near absorption ear stop near (layer or region or medium or film) and saturable near absorption ear stop near (layer or region or medium or film) and saturable near absorption ear stop near (layer or region or medium or film) an				,	
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clad\$ and (laser near diode) and (etch\$4 near stop near layer) Second			•	,	
near layer/ laser and clad\$4 and active and contact and electrode and (injection near2 stripe) and (etching near stop near (layer or region or medium or film)) 166 laser and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) 170 l(laser and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) 180 l(laser and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and 372/46 180 l(laser and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and 372/46) and saturatable near absorption 180 l(laser and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and 372/46) and saturatable near absorption 190 l(laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption and 372/46 2003/04/03 16:35				_	
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372/46) and saturatable near absorption 8 ((laser and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film))) and 372/46) and saturable near absorption 1 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption and 372/46 2 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 2 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 3 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 4 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 5 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 6 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 8 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption			electrode and (ridge or stripe) and (etching near stop	US-PGPUB;	
- 8 ((laser and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and 372/46) and saturable near absorption 1 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption and 372/46 2 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 2 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 3 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 4 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 5 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 6 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 8 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption	1				
Solution Comparison of the properties of the			372/46) and saturatable near absorption	•	
electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and 372/46) and saturable near absorption 1 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 2 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 3 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 4 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 5 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 6 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 7 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 8 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption					
near (layer or region or medium or film))) and 372/46) and saturable near absorption 1 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near sturable near absorption and 372/46 2 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 2 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 372/46 EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO] -	8		•	2003/04/03 16:35
372/46) and saturable near absorption 1 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near sturable near absorption and 372/46 2 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 2 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 372/46) 4 (laser near diode) and clad\$4 and active and contact uspending the stop near (layer or region or medium or film)) and saturable near absorption 5 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 6 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 7 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 8 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 9 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption	1				
- IlBM_TDB USPAT; and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption and 372/46 - IlBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO;	[
1 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 2 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 1 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and sturable near absorption 2 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 3 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 4 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 5 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 6 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or region or medium or film)) and saturable near absorption			372/46) and saturable near absorption		
and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption and 372/46 2 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 2 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 3 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 4 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 5 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 6 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 7 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption					
stop near (layer or region or medium or film)) and saturable near absorption and 372/46 2 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 2 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 3 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 4 EPO; JPO; DERWENT; IBM_TDB 5 USPAT; US	-	1		-	2003/08/12 10:03
saturable near absorption and 372/46 2 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption O (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption DERWENT; IBM_TDB US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO;					
- 2 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption - 0 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption IBM_TDB US-PGPUB; EPO; JPO; 2003/08/12 11:10 2003/08/12 11:09 2003/08/12 11:09 2003/08/12 11:09			· · · · · · · · · · · · · · · · · · ·		
2 (laser near diode) and clad\$4 and active and contact and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 2 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 2 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 2 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 2 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 3 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption 3 (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption			saturable near absorption and 372/46		
and electrode and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption O (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; OS-PGPUB; EPO; JPO;				_	
stop near (layer or region or medium or film)) and saturable near absorption O (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; USPAT; US-PGPUB; EPO; JPO;	-	2			2003/08/12 11:10
saturable near absorption DERWENT; IBM_TDB USPAT; Stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;					
O (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption IBM_TDB USPAT; US-PGPUB; EPO; JPO;					
O (laser near diode) and clad\$4 and active and (ridge or stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption USPAT; US-PGPUB; EPO; JPO;			saturable near absorption		
stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption US-PGPUB; EPO; JPO;					
or medium or film)) and saturable near absorption EPO; JPO;			(laser near diode) and clad\$4 and active and (ridge or	USPAT;	2003/08/12 11:09
	-	0	-		
and foreting pear? here\ and fifteed adi book\ ar DED\MENT.	-	0	stripe) and (etching near stop near (layer or region		
	-	0	stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption	EPO; JPO;	
feedback) IBM_TDB	-	0	stripe) and (etching near stop near (layer or region or medium or film)) and saturable near absorption and (grating near2 bars) and ((feed adj back) or	EPO; JPO; DERWENT;	·

				· · · · · · · · · · · · · · · · · · ·
-	0	(laser near diode) and clad\$4 and active and saturable near absorption and (grating near2 bars)	USPAT; US-PGPUB;	2003/08/12 11:09
:		and ((feed adj back) or feedback)	EPO; JPO; DERWENT;	
			IBM TDB	
-	0	((laser near diode) and clad\$4 and active and contact	USPAT;	2003/08/12 11:09
		and electrode and (ridge or stripe) and (etching near	US-PGPUB;	
		stop near (layer or region or medium or film)) and	EPO; JPO;	
		saturable near absorption) and grating near2 bar	DERWENT;	
			IBM_TDB	0000/00/10 11:00
-	1091	grating near2 bar	USPAT; US-PGPUB;	2003/08/12 11:09
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1091	grating near2 bars	USPAT;	2003/08/12 11:09
			US-PGPUB;	
			EPO; JPO;	
	-		DERWENT;	
	742	grating near bars	IBM_TDB USPAT;	2003/08/12 11:10
-	742	grating near bars	US-PGPUB;	2003/08/12 11.10
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5	(laser near diode) and clad\$4 and active and (grating	USPAT;	2003/08/15 07:03
		near2 bars)	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	4	laser and (clad with (current near injection near	USPAT;	2003/08/15 07:05
	_	stripe)) and electrode and contact	US-PGPUB;	2000,00,100,000
		,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	81	laser and (clad with (current near injection)) and	USPAT;	2003/08/15 07:06
		electrode and contact	US-PGPUB; EPO; JPO;	
		. ,	DERWENT;	
			IBM_TDB	
-	123	laser and (clad with (current near injection)) and	USPAT;	2003/08/15 07:43
		electrode	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	298	laser and (clad\$4 with (current near injection)) and	IBM_TDB USPAT;	2003/08/15 07:45
	2.30	electrode	US-PGPUB;	
			EPO; JPO;	
		·	DERWENT;	
			IBM_TDB	
-	298	laser and (clad\$4 with (current near injection)) and	USPAT;	2003/08/15 08:50
		electrode and clad\$4	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	2777	372/46.ccls.	USPAT;	2003/08/15 08:50
			US-PGPUB;	
			EPO; JPO;	
		· ·	DERWENT;	
			IBM_TDB	<u> </u>

-	131	372/46.ccls. and (clad\$4 with (current near	USPAT;	2003/08/15 09:03
		injection)) and electrode and clad\$4	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		·	IBM_TDB	
-	95	372/46.ccls. and (clad\$4 with (current near	USPAT;	2003/08/15 09:25
		injection)) and electrode and clad\$4	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	358	372/46.ccls. and (current near injection) and	USPAT;	2003/08/15 09:26
		electrode and clad\$4	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	263	(372/46.ccls. and (current near injection) and	USPAT;	2003/08/15 09:26
		electrode and clad\$4) not (372/46.ccls. and (clad\$4	EPO; JPO;	
		with (current near injection)) and electrode and	DERWENT;	
		clad\$4)	IBM_TDB	